

Characteristics :

- ◆ SiC-photodiode with extended wavelength range
- ◆ active area: 0,1 mm²
- ◆ spectral range: 220 ... 390 nm
- ◆ high UV-responsivity: 0,18 A/W
- ◆ hermetically sealed TO-package
- ◆ option for isolated assembly of photodiode
- ◆ UT-option for extended operating temperature range 250°C
- ◆ RoHS, REACH and WEEE conform

**Applications :**

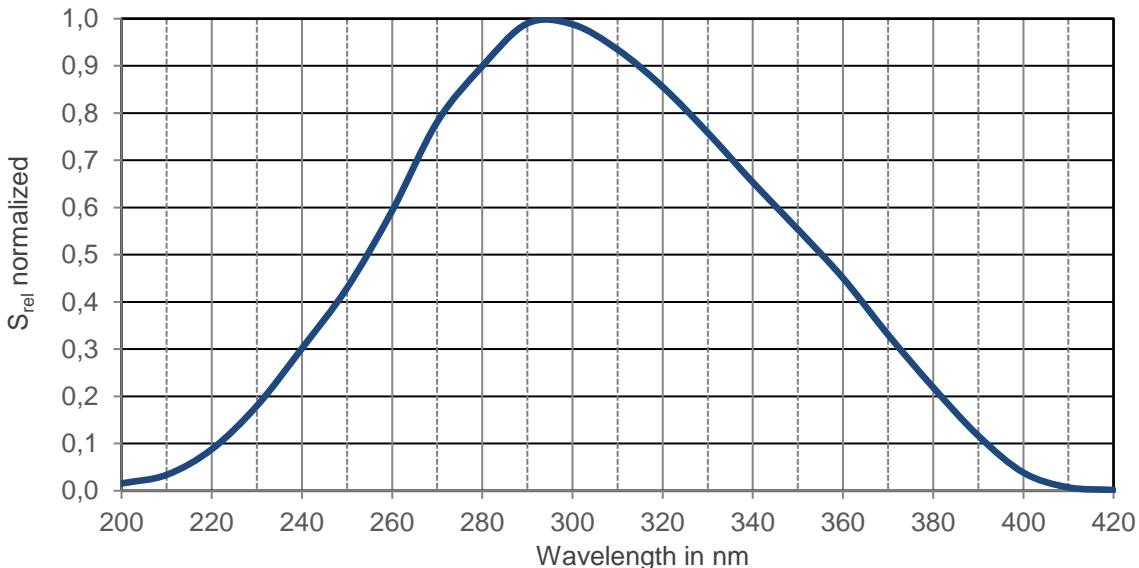
- ◆ optical measurements in UV-range
- ◆ control of sterilization lamps
- ◆ flame control

Absolute Maximum Ratings :

- | | |
|----------------------------------|--------------------|
| ◆ reverse voltage U _R | 20 V |
| ◆ operating temperature range | - 40 °C ... 150 °C |
| ◆ storage temperature range | - 40 °C ... 150 °C |
| ◆ soldering temperature (3s) | 260 °C |

Versions:

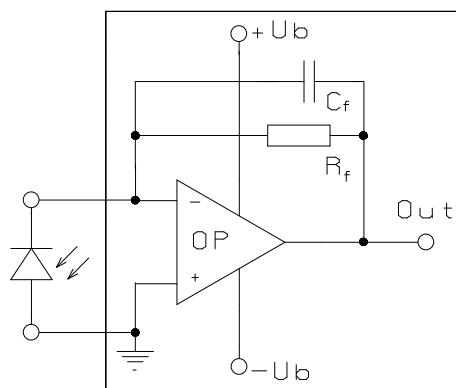
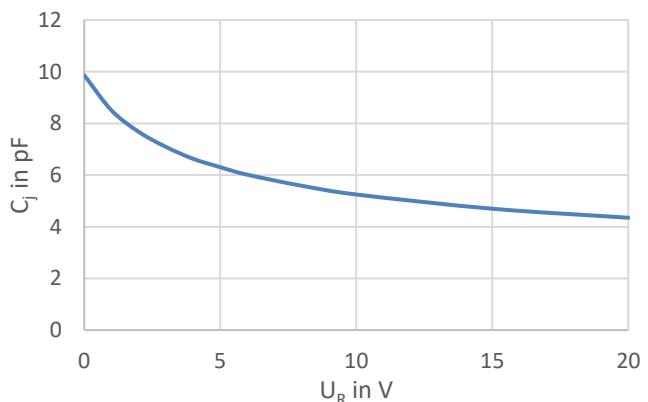
Package	Anode: isolated Cathode: case	Anode: isolated Cathode: case	Cathode, Anode : isolated + case-ground-pin	Operating Temperature up to 250 °C
TO5	JEA0,1X	JEAC0,1X	JEA0,1XI	*-UT
TO18	JEA0,1X-S	JEAC0,1X-S	JEA0,1XISZ	
TO52	JEA0,1X-SS	JEAC0,1X-SS	JEA0,1XISSZ	

Relativ Spectral Responsivity S_{rel}:

Rev. 2 (12/2020)

Technical Data :

Parameter	Test condition	TO5	TO18	TO52	Unit
active area		0,365 x 0,365			mm ²
spectral range	λ_{short} λ_{long}	$S = 0,1 \times S_{\text{max}}$	222 392		nm nm
wavelenght of peak response			292		nm
peak response S_{max}	$\lambda = 292 \text{ nm}$		190		mA/W
spectral response $S_{254\text{nm}}$	$\lambda = 254 \text{ nm}$		95		mA/W
dark current I_R	$U_R = 1 \text{ V}$		10		fA
junction capacitance C_j	$f = 10 \text{ kHz}$		10		pF
field of view (FOV)	Anode isolated Cathode isolated Both isolated	± 48 ± 51 ± 52	± 26 ± 27 ± 29	± 40 ± 43 ± 46	degree
weight		0,8	0,3	0,3	gram
package drawing	Anode isolated Cathode isolated Both isolated	TO5 TO5 TO5 iso.	TO18 TO18 TO18 iso.	TO52 TO52 TO52 iso.	

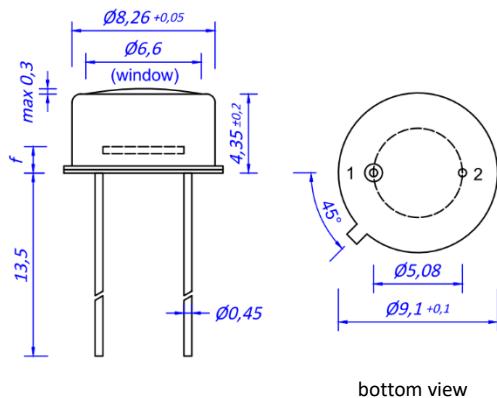
 test conditions, as not otherwise specified: $T_A = 25 \text{ }^\circ\text{C}$, $U_R = 0 \text{ V}$
Application Example

Junction Capacitance C_j vs. Reverse Voltage U_R :


The application example shows a typical circuit. R_f is responsible for the gain of the circuit. C_f compensates the reverse junction capacitance of the photodiode and the input capacitance of the opamp. The exact value of C_f depends on R_f , used opamp and capacitance of the circuit. A typical value is 1pF.

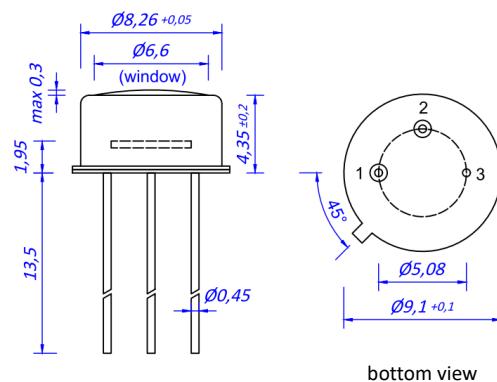
The chart shows the typical dependence of junction capacitance C_j vs. applied reverse voltage U_R . Lower intrinsic capacitance can be used to increase the bandwidth (lower the rise time) in electric circuits.

Case Dimensions:

TO5



TO5 isolated

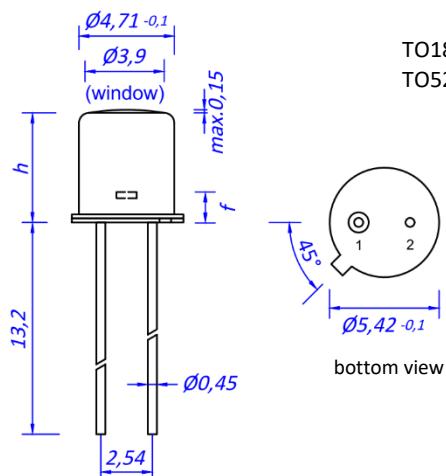


JEA0,1X: Pin 1: Anode
 Pin 2: Cathode + Case
 $f = 1,6 \text{ mm}$

JEA0,1XI: Pin 1: Anode
 Pin 2: Cathode
 Pin 3: Case

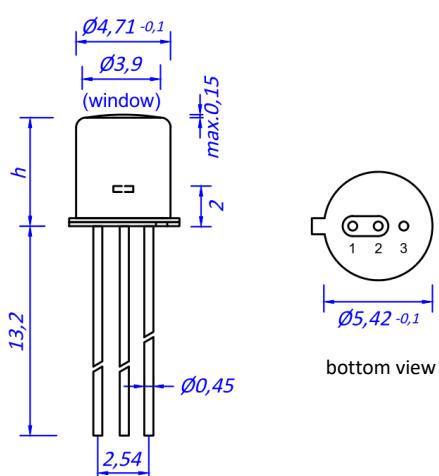
JEAC0,1X: Pin 1: Cathode
 Pin 2: Anode + Case
 $f = 1,85 \text{ mm}$

TO18 / TO52



TO18: $h = 5,2 \text{ mm} \pm 0,1 \text{ mm}$
 TO52: $h = 3,7 \text{ mm} \pm 0,1 \text{ mm}$

TO18 / TO52 isolated



JEA0,1S/SS: Pin 1: Anode
 Pin 2: Cathode + Case
 $f = 1,5 \text{ mm}$

JEA0,1XISZ/ISSZ: Pin 1: Anode
 Pin 2: Cathode
 Pin 3: Case

JEAC0,1X-S/SS: Pin 1: Cathode
 Pin 2: Anode + Case
 $f = 1,75 \text{ mm}$